SOC COM

18. A method according to any one of claims 1, 2, 9 and 10, wherein said semiconductor layer comprises silicon and germanium.

- 19. A method according to any one of claims 1, 2, 9 and 10, wherein the crystallized semiconductor layer contains carbon at a concentration not higher than $5 \times 10^{18} \text{atoms/cm}^3$.
- 20. A method according to any one of claims 1, 2, 9 and 10, wherein the crystallized semiconductor layer contains oxygen at a concentration not higher than $5 \times 10^{19} a toms/cm^3$. --